

Project A2 'Spintronics'

A2.3 'Spin Injection, Manipulation, and Read-Out' (H. Kalt, M. Hetterich)

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A2.5 'Structural and Chemical Properties of Quantum Dot Structures' (D. Gerthsen, D. Litvinov)

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A2.8 'Optical Microcavities' (H. Kalt, M. Hetterich)

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